



### Typical Applications

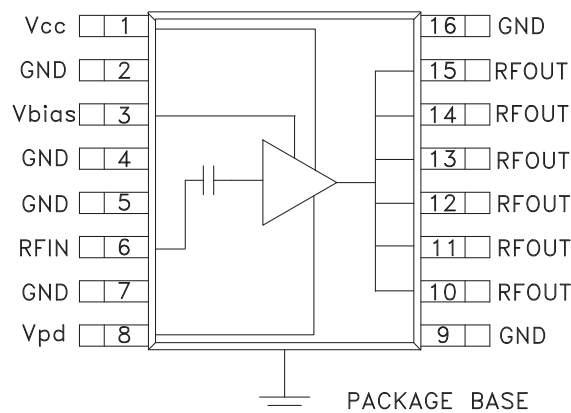
The HMC457QS16G / HMC457QS16GE is ideal for applications requiring a high dynamic range amplifier:

- CDMA & W-CDMA
- GSM, GPRS & Edge
- Base Stations & Repeaters

### Features

- Output IP3: +46 dBm
- Gain: 27 dB @ 1900 MHz
- 48% PAE @ +32 dBm Pout
- +25 dBm W-CDMA Channel Power @ -50 dBc ACPR
- Integrated Power Control (Vpd)
- QSOP16G SMT Package: 29.4 mm<sup>2</sup>
- Included in the HMC-DK002 Designer's Kit

### Functional Diagram



### General Description

The HMC457QS16G & HMC457QS16GE are high dynamic range GaAs InGaP Heterojunction Bipolar Transistor (HBT) 1 watt MMIC power amplifiers operating between 1.7 and 2.2 GHz. Packaged in a miniature 16 lead QSOP plastic package, the amplifier gain is typically 27 dB from 1.7 to 2.0 GHz and 25 dB from 2.0 to 2.2 GHz. Utilizing a minimum number of external components, the amplifier output IP3 can be optimized to +45 dBm. The power control (Vpd) can be used for full power down or RF output power/current control. The high output IP3 and PAE make the HMC457QS16G & HMC457QS16GE ideal power amplifiers for Cellular/3G base station & repeater applications.

### Electrical Specifications, $T_A = +25^\circ\text{C}$ , $V_S = +5\text{V}$ , $V_{pd} = +5\text{V}$ , $V_{bias} = +5\text{V}$ [1]

Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range	1710 - 1990		2010 - 2170				MHz
Gain	24	27		22	25		dB
Gain Variation Over Temperature		0.025	0.035		0.025	0.035	dB / °C
Input Return Loss		11			11		dB
Output Return Loss		8			5		dB
Output Power for 1dB Compression (P1dB)	26	29		27.5	30.5		dBm
Saturated Output Power (P <sub>sat</sub> )		32.5			32		dBm
Output Third Order Intercept (IP3) [2]	42	45		42	45		dBm
Noise Figure		6			5		dB
Supply Current (I <sub>cc</sub> )		500			500		mA
Control Current (I <sub>pd</sub> )		4			4		mA
Bias Current (V <sub>bias</sub> )		10			10		mA

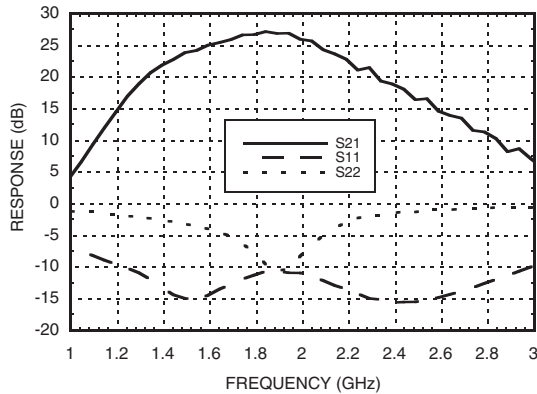
[1] Specifications and data reflect HMC457QS16G measured using the respective application circuits for each designated frequency band found herein. Contact the HMC Applications Group for assistance in optimizing performance for your application.

[2] Two-tone output power of +15 dBm per tone, 1 MHz spacing.

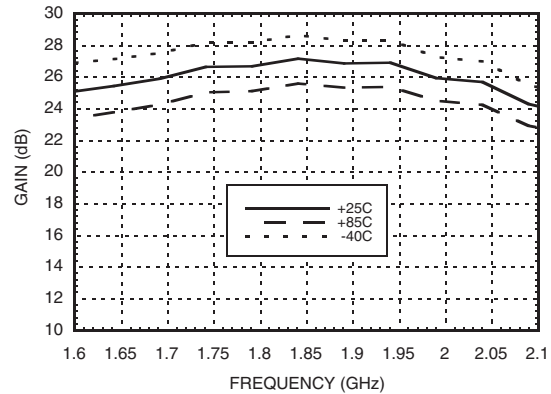


**InGaP HBT 1 WATT POWER  
AMPLIFIER, 1.7 - 2.2 GHz**

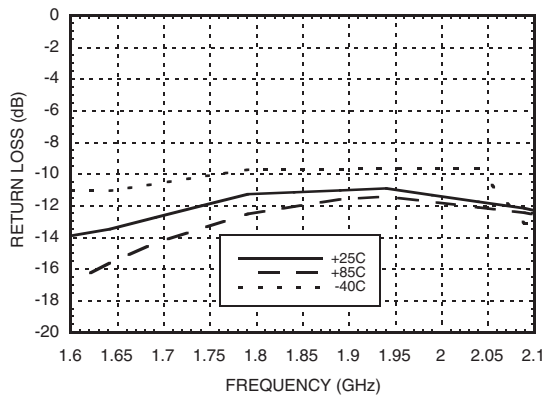
**Broadband Gain  
& Return Loss @ 1900 MHz**



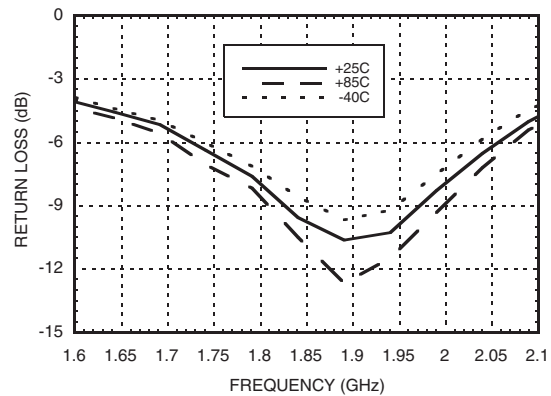
**Gain vs. Temperature @ 1900 MHz**



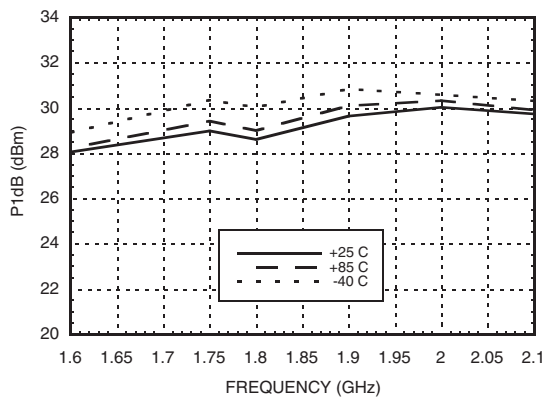
**Input Return Loss  
vs. Temperature @ 1900 MHz**



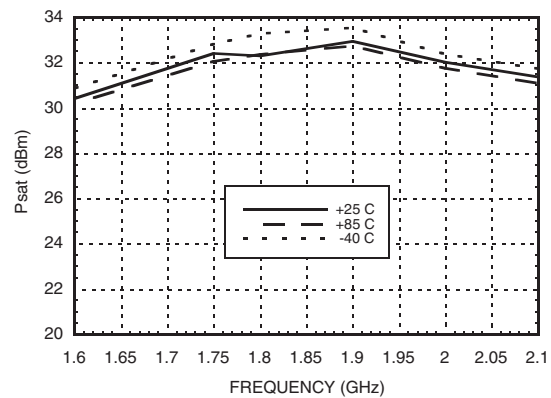
**Output Return Loss  
vs. Temperature @ 1900 MHz**



**PIdB vs. Temperature @ 1900 MHz**



**Psat vs. Temperature @ 1900 MHz**



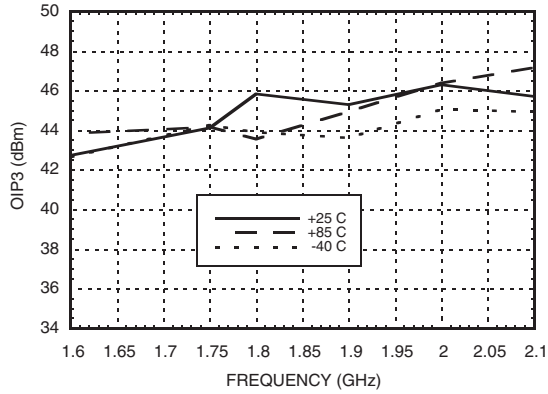
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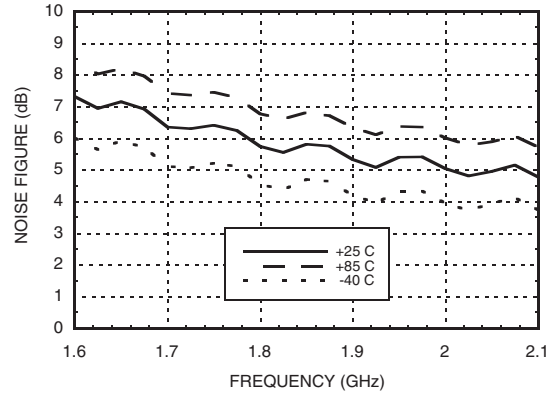


**InGaP HBT 1 WATT POWER AMPLIFIER, 1.7 - 2.2 GHz**

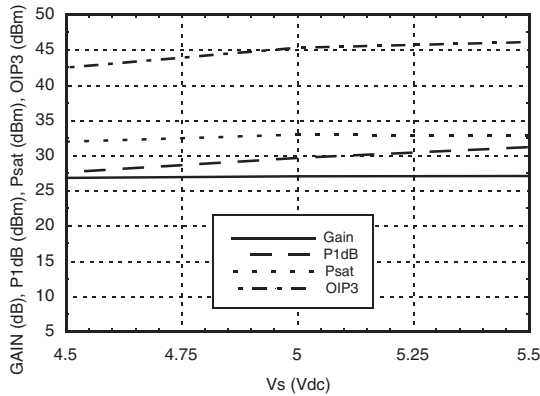
**Output IP3 vs. Temperature @ 1900 MHz**



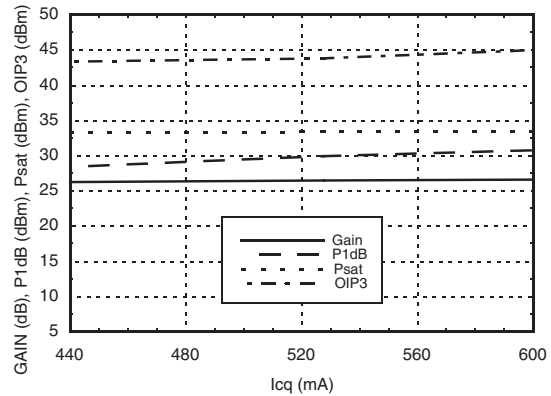
**Noise Figure vs. Temperature @ 1900 MHz**



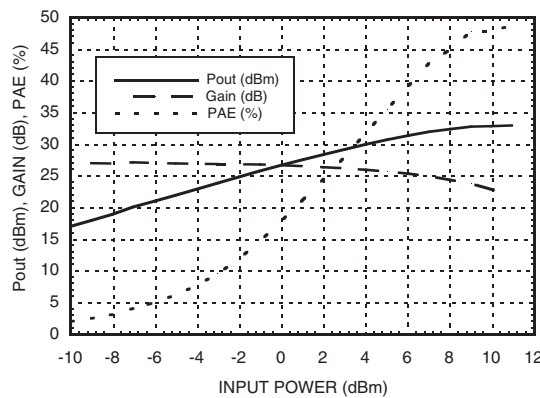
**Gain, Power & IP3 vs. Supply Voltage @ 1900 MHz**



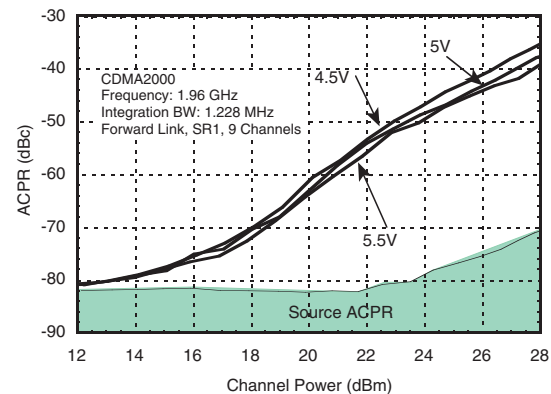
**Gain, Power & IP3 vs. Supply Current @ 1900 MHz\***



**Power Compression @ 1900 MHz**



**ACPR vs. Supply Voltage @ 1960 MHz CDMA 2000, 9 Channels Forward**



\* Icq is controlled by varying Vpd.

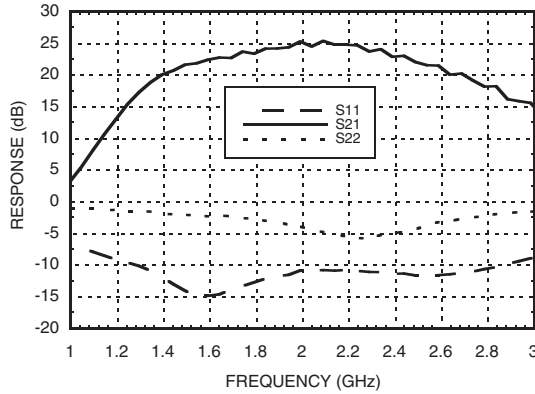
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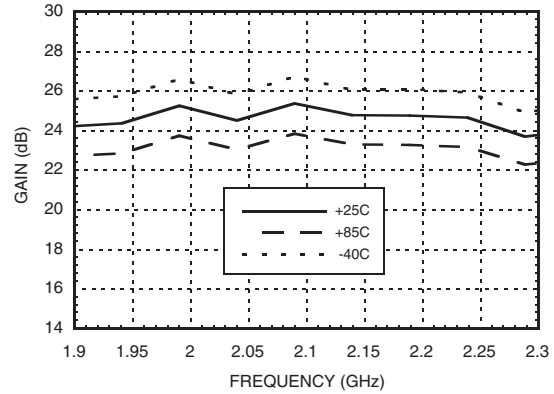


**InGaP HBT 1 WATT POWER  
AMPLIFIER, 1.7 - 2.2 GHz**

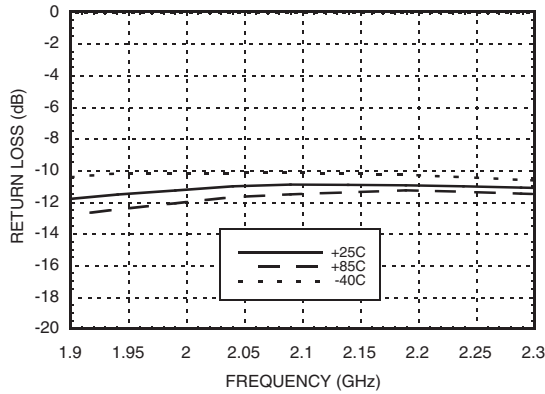
**Broadband Gain  
and Return Loss @ 2100 MHz**



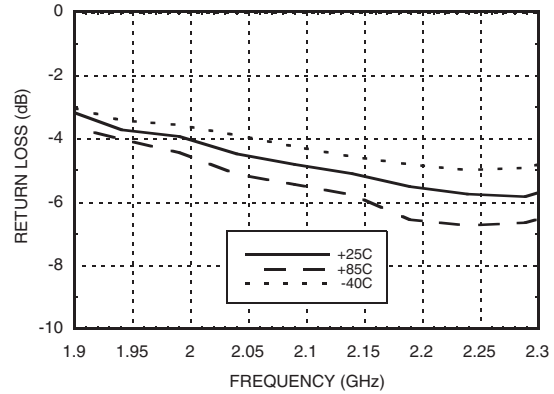
**Gain vs. Temperature @ 2100 MHz**



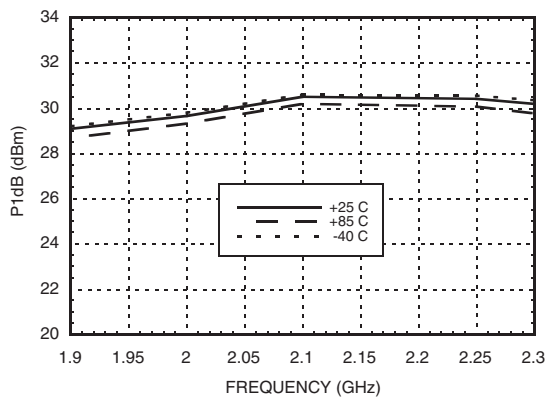
**Input Return Loss  
vs. Temperature @ 2100 MHz**



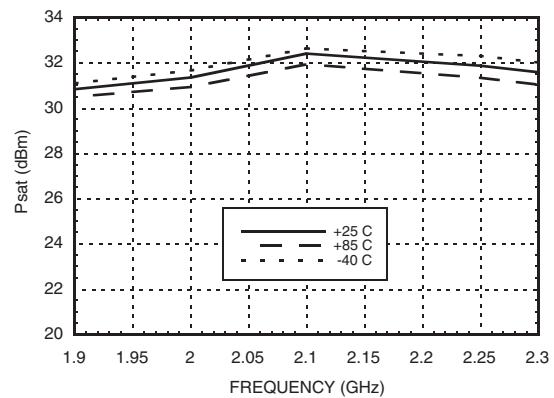
**Output Return Loss  
vs. Temperature @ 2100 MHz**



**PldB vs. Temperature @ 2100 MHz**



**Psat vs. Temperature @ 2100 MHz**



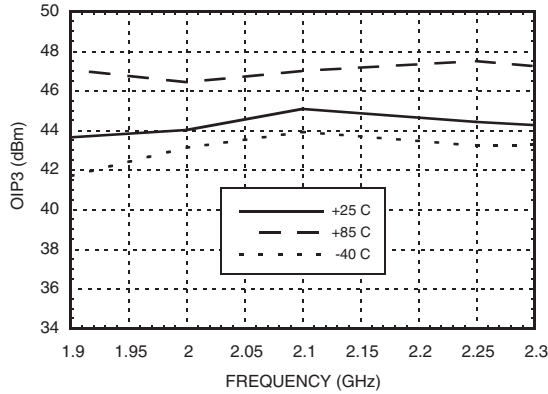
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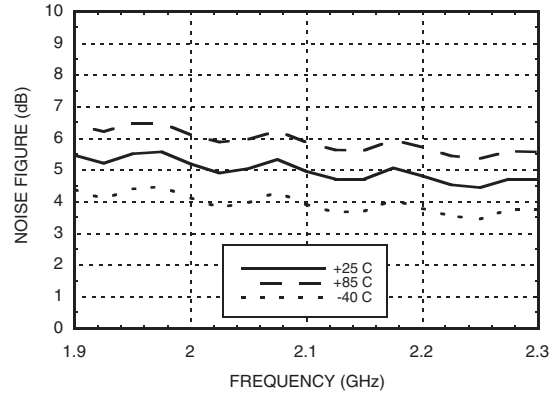


**InGaP HBT 1 WATT POWER AMPLIFIER, 1.7 - 2.2 GHz**

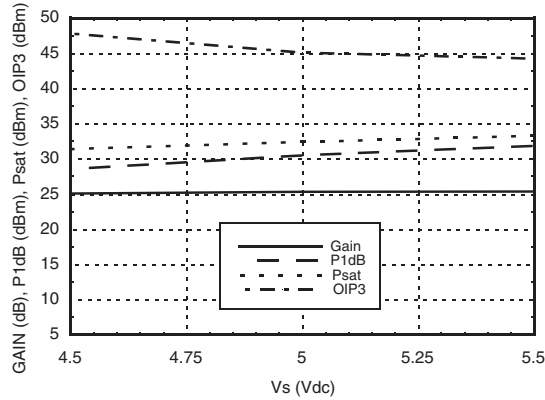
**Output IP3 vs. Temperature @ 2100 MHz**



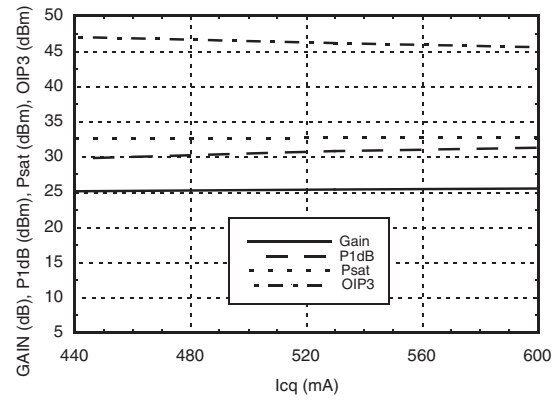
**Noise Figure vs. Temperature @ 2100 MHz**



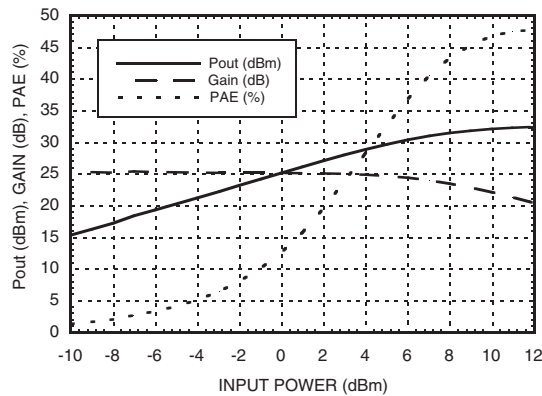
**Gain, Power & IP3 vs. Supply Voltage @ 2100 MHz**



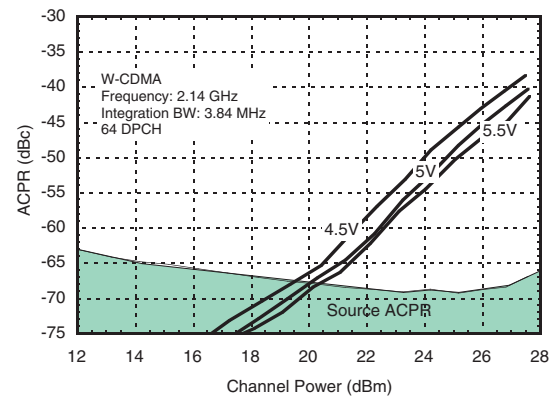
**Gain, Power & IP3 vs. Supply Current @ 2100 MHz\***



**Power Compression @ 2100 MHz**



**ACPR vs. Supply Voltage @ 2140 MHz W-CDMA, 64 DPCH (Uplink)**



\*Icq is controlled by varying Vpd

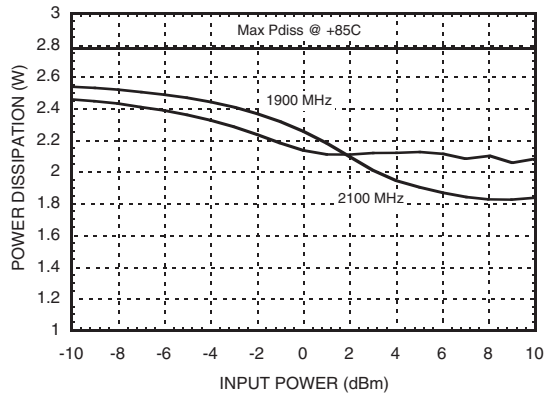
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## InGaP HBT 1 WATT POWER AMPLIFIER, 1.7 - 2.2 GHz



### Power Dissipation



### Absolute Maximum Ratings

Collector Bias Voltage (Vcc)	+6 Vdc
Control Voltage (Vpd)	+5.4 Vdc
RF Input Power (RFIN)(Vs = Vpd = +5 Vdc)	+15 dBm
Junction Temperature	150 °C
Continuous P <sub>diss</sub> (T = 85 °C) (derate 42.9 mW/°C above 85 °C)	2.78 W
Thermal Resistance (junction to ground paddle)	23.3 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

### Typical Supply Current vs. Supply Voltage

V <sub>s</sub> (V)	I <sub>cq</sub> (mA)
4.5	400
5.0	510
5.5	620



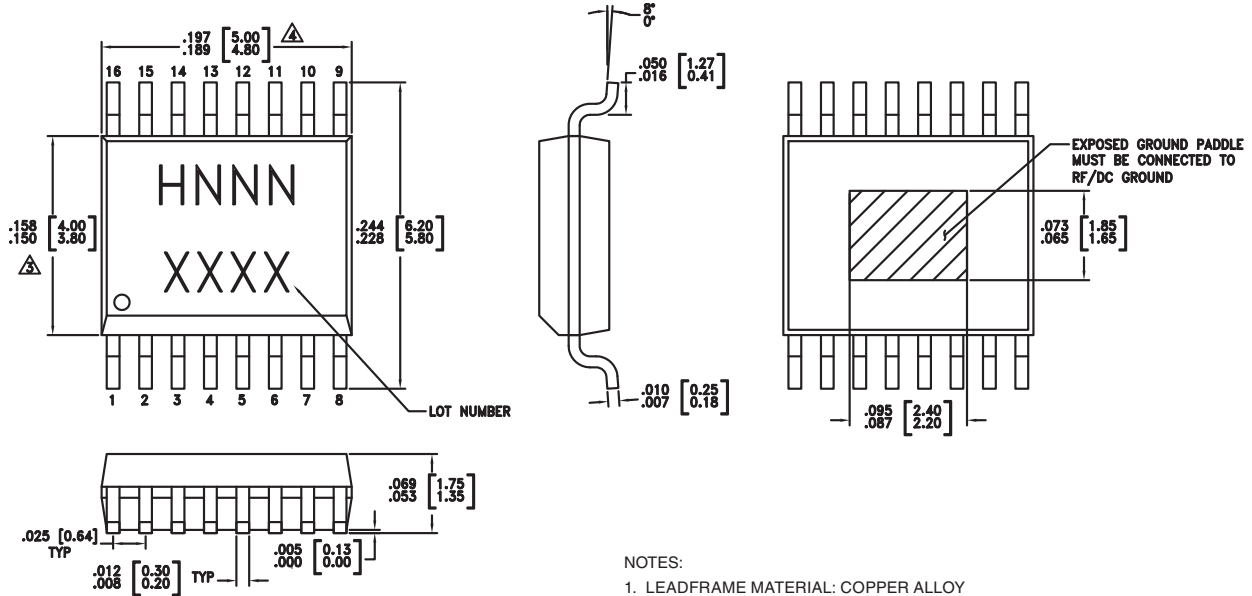
ELECTROSTATIC SENSITIVE DEVICE  
OBSERVE HANDLING PRECAUTIONS

11

LINEAR & POWER AMPLIFIERS - SMT



**Outline Drawing**



**NOTES:**

1. LEADFRAME MATERIAL: COPPER ALLOY
2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- ⚠ DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
- ⚠ DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
5. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

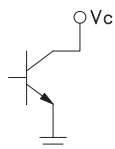

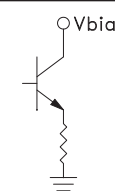
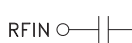
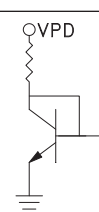
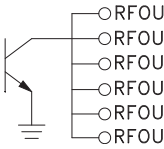
**Package Information**

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking <sup>[3]</sup>
HMC457QS16G	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 <sup>[1]</sup>	H457 XXXX
HMC457QS16GE	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 <sup>[2]</sup>	H457 XXXX

[1] Max peak reflow temperature of 235 °C  
 [2] Max peak reflow temperature of 260 °C  
 [3] 4-Digit lot number XXXX



### Pin Descriptions

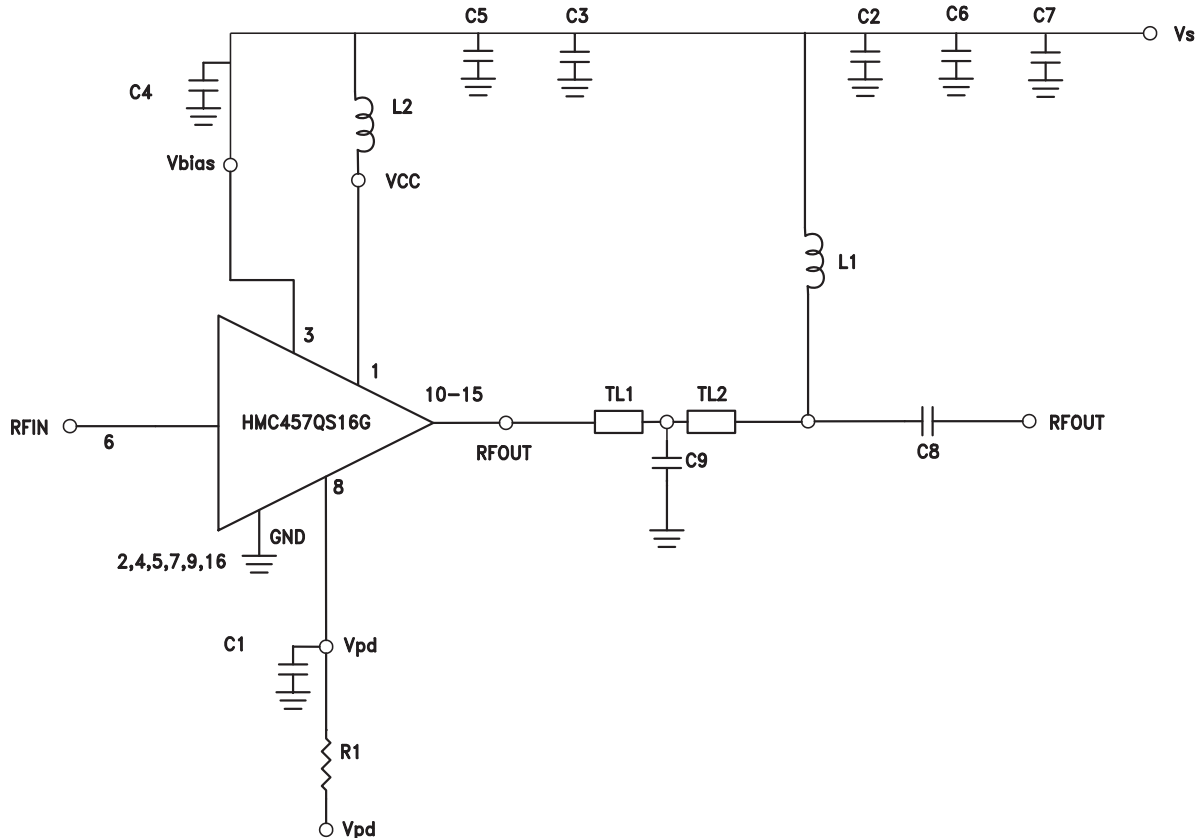
Pin Number	Function	Description	Interface Schematic
1	Vcc	Power supply voltage for the first amplifier stage. External bypass capacitors are required as shown in the application schematic.	
2, 4, 5, 7, 9, 16	GND	Ground: Backside of package has exposed metal ground slug that must also be connected to RF/DC ground. Vias under the device are required.	
3	Vbias	Power Supply for Bias Circuit	
6	RFIN	This pin is AC coupled and matched to 50 Ohms	
8	Vpd	Power control pin. For maximum power, this pin should be connected to +5V. A higher voltage is not recommended. For lower idle current, this voltage can be reduced.	
10 - 15	RFOUT	RF output and DC bias for the output stage.	





**1900 & 2100 MHz Application Circuit**

This circuit was used to specify the performance for 1900 & 2100 MHz operation. Contact the HMC Applications Group for assistance in optimizing performance for your application.



	TL1	TL2
Impedance	50 Ohm	50 Ohm
Physical Length	0.170"	0.080"
Electrical Length	20°	9°
PCB Material: 10 mil Rogers 4350, Er = 3.48		

Recommended Component Values	1900 MHz	2100 MHz
C1 - C4	100 pF	100 pF
C5, C6	1000 pF	1000 pF
C7	2.2 μF	2.2 μF
C8	33 pF	33 pF
C9	3.9 pF	2.7 pF
L1, L2	3.9 nH	3.9 nH
R1	160 Ohm	160 Ohm